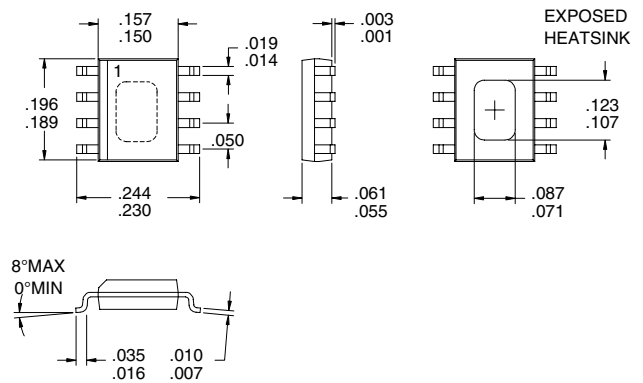


**Typical Applications**

- PCS Communication Systems
- 2.5GHz ISM Band Applications
- Wireless LANs
- Commercial and Consumer Systems
- Portable Battery Powered Equipment

**Product Description**

The RF2128P is a medium-power, high-efficiency, linear amplifier IC. The device is manufactured on an advanced Gallium Arsenide Heterojunction Bipolar Transistor (HBT) process, and has been designed for use as the final RF amplifier in 2.45GHz ISM applications such as WLAN and POS terminals. The part also will function as the final stage in digital PCS phone transmitters requiring linear amplification operating between 1900MHz and 2200MHz, with over 100mW transmitted power, or as the driver stage for the RF2125 high power amplifier. A simple power down function is included for TDD operation. The part is packaged in a low-cost plastic package with a metal backside.



Refer to "Handling of PSOP and PSSOP Products" on page 16-15 for special handling information.

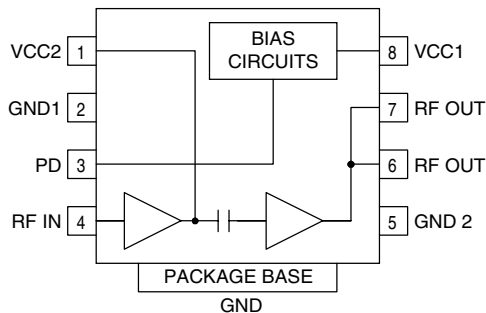
**Optimum Technology Matching® Applied**

- Si BJT       GaAs HBT       GaAs MESFET  
 Si Bi-CMOS       SiGe HBT       Si CMOS

**Package Style: PSOP-8**

**Features**

- Single 3.0V to 6.5V Supply
- 100mW Linear Output Power
- 28dB Small Signal Gain
- 33% Efficiency
- Digitally Controlled Power Down Mode
- 1900MHz to 2500MHz Operation



**Functional Block Diagram**

**Ordering Information**

- RF2128P Medium Power Linear Amplifier  
 RF2128P PCBA Fully Assembled Evaluation Board

RF Micro Devices, Inc.  
 7625 Thorndike Road  
 Greensboro, NC 27409, USA

Tel (336) 664 1233  
 Fax (336) 664 0454  
<http://www.rfmd.com>

# RF2128P

## Absolute Maximum Ratings

Parameter	Rating	Unit
Supply Voltage ( $V_{CC}$ )	-0.5 to +7.5	$V_{DC}$
Power Down Voltage ( $V_{PD}$ )	-0.5 to +5.5	V
DC Supply Current	125	mA
Input RF Power	+12	dBm
Output Load	20:1	
Operating Ambient Temperature	-40 to +85	$^{\circ}C$
Storage Temperature	-40 to +150	$^{\circ}C$

Refer to "Handling of PSOP and PSSOP Products" on page 16-15 for special handling information.



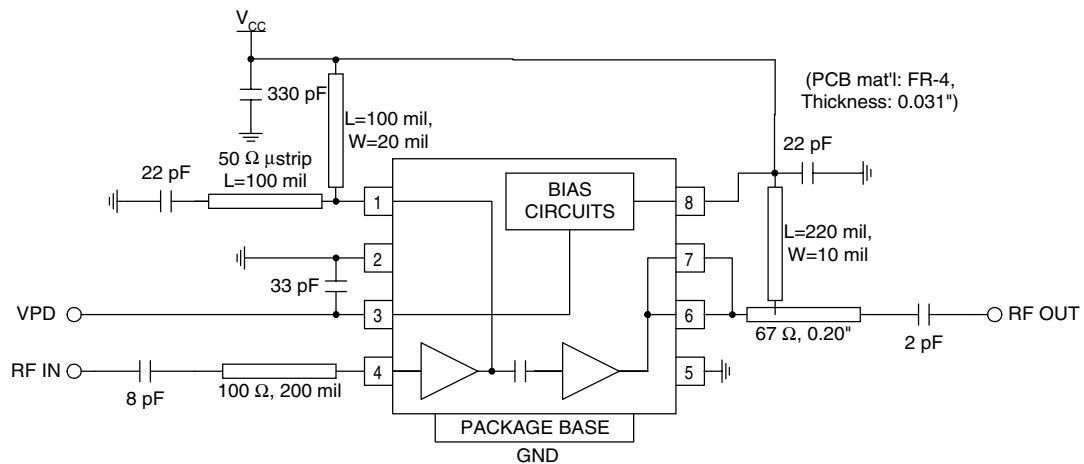
**Caution!** ESD sensitive device.

RF Micro Devices believes the furnished information is correct and accurate at the time of this printing. However, RF Micro Devices reserves the right to make changes to its products without notice. RF Micro Devices does not assume responsibility for the use of the described product(s).

Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
<b>Overall</b>					
Frequency Range		1900 to 2500		MHz	$T=25^{\circ}C$ , $V_{CC}=5V$ , $V_{PD}=5.0V$ , Freq=2400MHz
Maximum Output Power		+22		dBm	$V_{CC}=5.0V$ , $V_{PD}=5.0V$ , $P_{IN}=-3.0dBm$
1dB Compression Output Power		>+24		dBm	$V_{CC}=6.0V$ , $V_{PD}=5.5V$ , $P_{IN}=0dBm$
Total CW Efficiency		+21		dBm	Maximum output
Small-signal Gain		33		%	
Second Harmonic		28		dB	
Third Harmonic		-23		dBc	
Isolation		-19		dBc	
Input VSWR		15		dB	$V_{PC}=0.2V$
Input Impedance		2:1		$\Omega$	
Noise Figure		50		dB	
<b>Two-tone Specification</b>					
Average Two-Tone Power		+17		dBm	PEP-3dB
IM <sub>3</sub>		-27		dBc	$P_{OUT}=+14dBm$ for each tone
IM <sub>5</sub>		-40		dBc	$P_{OUT}=+14dBm$ for each tone
IM <sub>7</sub>		-44		dBc	$P_{OUT}=+14dBm$ for each tone
Two-Tone Power-Added Efficiency		30		%	
<b>Power Down Control</b>					
Power Down "ON"		$V_{CC}$		V	Voltage supplied to the input; device is "on"
Power Down "OFF"	0		1.2	V	Voltage supplied to the input; device is "off"
<b>Power Supply</b>					
Voltage		5		V	Specifications
		3.0 to 6.5		V	Operating
Current		50	65	mA	Operating Idle
		85		mA	At maximum output power
Current			10	$\mu A$	Power Down

Pin	Function	Description	Interface Schematic
1	<b>VCC2</b>	Power supply for the driver stage and interstage matching. External matching on this pin is required to optimize the gain. The matching on this port also greatly affects the input impedance. A decoupling capacitor of 330pF is required, together with a series RC for tuning for maximum gain at the desired frequency. See the application information for details.	
2	<b>GND1</b>	Ground connection for the driver stage. Keep traces physically short and connect immediately to the ground plane for best performance.	
3	<b>PD</b>	Power Down control. When this pin is "low", all circuits are shut off. A "low" is typical 1.2V or less at room temperature. When this pin is "high", all circuits are operating normally. A "high" is $V_{CC}$ . If PD is below $V_{CC}$ output power and performance will be degraded. This could be used to obtain some gain control, but results are not guaranteed.	
4	<b>RF IN</b>	RF Input. This is a 50Ω input, but the actual impedance depends on the matching provided on pin 1. An external DC blocking capacitor is required if this port is connected to a DC path to ground.	
5	<b>GND2</b>	Ground connection for the output stage. Keep traces physically short and connect immediately to the ground plane for best performance.	
6	<b>RF OUT</b>	RF Output and power supply for the output stage. Bias for the output stage needs to be provided on this pin. This can be done through a quarter-wave microstrip that is RF grounded on the other end. For matching to 50Ω, an external series microstrip line is required.	
7	<b>RF OUT</b>	Same as pin 6.	
8	<b>VCC1</b>	Power supply for the bias circuits. An external RF bypass capacitor of 22pF is required. Keep the traces to the capacitor as short as possible, and connect the capacitor immediately to the ground plane.	
<b>Pkg Base</b>	<b>GND</b>	Ground connection. The backside of the package should be connected to the ground plane through a short path, i.e., vias under the device may be required.	

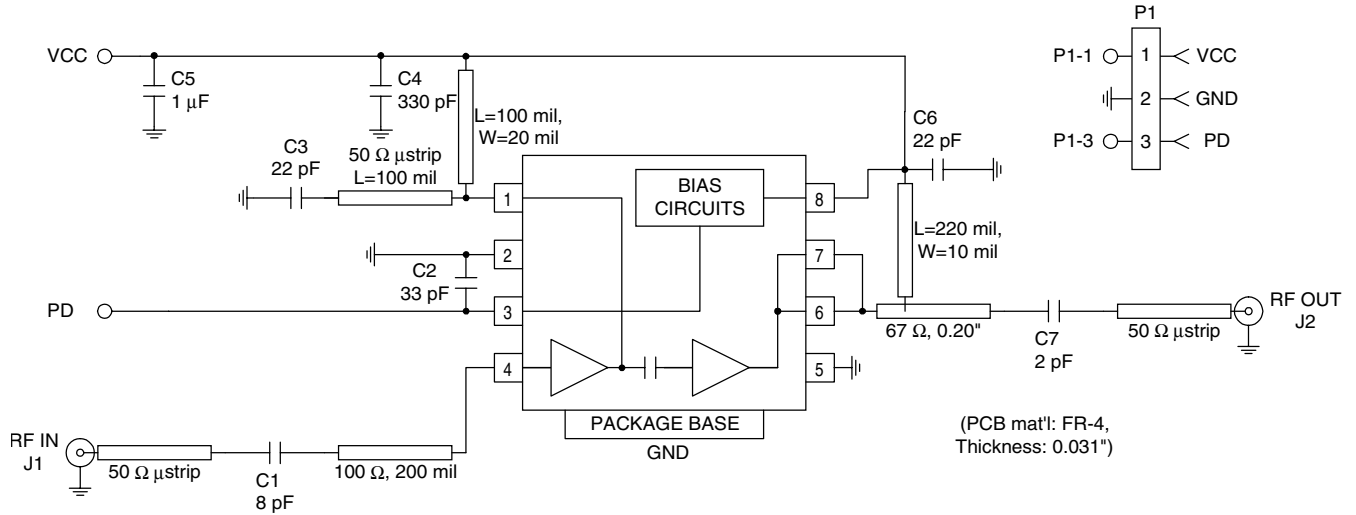
## Application Schematic 2450MHz Operation



## Evaluation Board Schematic 2450MHz Operation

(Download [Bill of Materials](http://www.rfmd.com) from [www.rfmd.com](http://www.rfmd.com).)

2128401 Rev C



## Evaluation Board Layout 1.572" X 1.121"

